Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	("20050253519").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/14 10:56
S2 .	198115	(PDP (plasma (gas near3 discharge)) near3 (device discharge panel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 10:57
S3	454675	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 10:59
S4	26967	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) same ((silicon Si silica) and (carbon C))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 17:50
S5	1722	S2 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 11:01
S6 .	9305	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) with ((silicon Si silica) and (carbon C))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 11:01
S7	737	S2 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 11:03
S8	2328	(313/582-587).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/14 11:03
S9 ;	899	(313/586-587).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/15 16:24

S10	12	S9 and S7	US-PGPUB;	OR	ON	2006/08/14 17:44
210	12	35 and 37	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		ON	2000/00/17 17.77
S11;	3	"2001110321"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 11:17
S12	1	2001-567516.NRAN.	DERWENT	OR	ON	2006/08/14 11:16
S13	0	"200471338"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 11:17
S14	5	"2004071338"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 11:17
S15	1	("20040027072").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/14 11:37
S16	0	("2004/0027072").URPN.	USPAT	OR	ON	2006/08/14 11:53
S19	1	("5454861").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/14 12:43
S20	0	("2005/0253519").URPN.	USPAT	OR	ON	2006/08/14 15:53
S21	15	S8 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 17:44
S22	3	S21 not S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 17:45

S23	26967	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) same ((silicon Si silica) and (carbon "C"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/14 17:51
S24	26344	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) same ((silicon Si silica) and (carbon "C"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/14 17:53
S25	20357	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) same (silicon Si silica) same (carbon "C")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/14 17:53
S26	9	("5791960" "6034474" "6218784" "6407509" "6437507" "6522081").PN. OR ("6657396"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/14 18:07
S27	198189	(PDP (plasma (gas near3 discharge)) near3 (device discharge panel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:19
S28	9310	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) with ((silicon Si silica) and (carbon C))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:08
S29:	738	S27 and S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:00
S30	2333	(313/582-587).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/15 11:00
S31	15	S30 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:00

S32	723	S29 not S31	US-PGPUB;	OR	ON	2006/08/15 11:01
	723	329 1101 331	USPAT; USOCR; EPO; JPO; DERWENT;		ON	2000/00/13 11:01
			IBM_TDB	:		
S33	5325	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) with (silicon Si silica) with (carbon C)	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2006/08/15 11:15
			DERWENT; IBM_TDB			
S34	451	S27 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:09
S35	5325	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) with (silicon Si silica) with (carbon "C")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:16
S36	3376	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) with (silicon Si silica) with (carbon sic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:17
S37	5120	(buffer protect\$3 MgO) near2 (film layer\$3 coat\$3) with (sic or ((silicon Si silica) with (carbon)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:17
S38 ⁻	411	S27 and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:17
S39;	79990	(PDP (plasma near3 (device panel)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:20

S40	145	S37 and S39	US-PGPUB; USPAT;	OR	ON	2006/08/15 11:20
:			USOCR; EPO; JPO; DERWENT; IBM_TDB			
S41	1	("2001/0048275").URPN.	USPAT	OR	ON	2006/08/15 11:57
S42	1	("6657396 ").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/15 12:03
S43	2	"2005166400"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:04
S44	7	"2005005250"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:10
S45	3	"2001110321"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:11
S46	0	("9and(sic(siliconnearcarbide))with(mgo(magnesiumnearoxide))").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/15 16:25
S47	901	(313/586-587).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/15 16:25
S48	3	S47 and (sic (silicon near carbide)) with (mgo (magnesium near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 16:26
S49	2333	(313/582-587).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/15 16:26
S50	6	S49 and (sic (silicon near carbide)) with (mgo (magnesium near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 16:26

S51	1	("6171438").PN.	US-PGPUB;	OR	OFF	2006/08/15 16:29
			USPAT;		i }	
			USOCR			